

### Description

The HTH2D25P300H is an internally Input/Output pre-matched discrete GaN on SiC HEMT Power Amplifier with 300W saturated output power covering frequency range from 2.4 to 2.5 GHz.

### Features

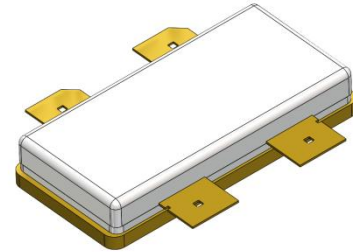
- Operating Frequency Range: 2.4 - 2.5 GHz
- Operating Drain Voltage: 48V
- Saturation Output Power: 300W
- Excellent thermal stability due to low thermal resistance package
- Enhanced robustness design without device degradation
- Internally integrated enhanced ESD design

### Applications

- RF Industrial Heating and Drying
- Solid-state Commercial and Industrial Cooking
- Plasma Lighting
- Semiconductor Equipment
- Automotive Ignition
- Medical & Scientific Sciences

### Ordering Information

Part Number	Description
HTH2D25P300H	Tray Package
HTH2D25P300H EVB	2.4-2.5 GHz EVB

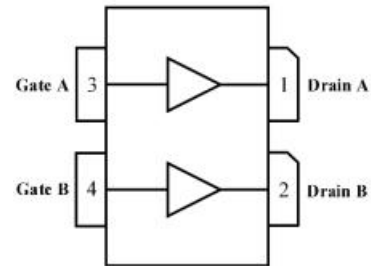


**ACC2110S-4L**

Earless Flanged Balanced  
Air Cavity Ceramic Package; 4 Leads



**HTH2D25P300H**



(Top View)

Note: Exposed backside of the package is the source terminal for the transistor

**Pin Connections**

### Typical Performance

#### RF Characteristics (Pulsed-CW)

Freq (MHz)	P3dB (dBm)	P3dB (W)	Gain (dB)	Eff(%)@P3dB
2400	56.0	398	19.8	74.6
2450	55.4	347	19.0	74.9
2500	54.8	302	18.2	74.3

Test conditions unless otherwise noted: 25 °C, VDD = +48Vdc, IDQ =100mA, PW = 100us, Duty Cycle= 10%, tested on WATECH Application Board

#### RF Characteristics (CW)

Freq (MHz)	P3dB (dBm)	P3dB (W)	Gain (dB)	Eff(%)@P3dB
2400	55.6	363	19.1	72.1
2450	55.1	324	18.8	72.3
2500	54.9	309	17.3	71.5

Test conditions unless otherwise noted: 25 °C, VDD = +48Vdc, IDQ =100mA, CW, tested on WATECH Application Board

### Absolute Maximum Ratings

Parameter	Range/Value	Unit
Drain voltage (V <sub>DSS</sub> )	0 to 130	V
Gate voltage (V <sub>GS</sub> )	-10 to 2	V
Storage Temperature (T <sub>STG</sub> )	-55 to 150	°C
Junction Temperature (T <sub>J</sub> )	225	°C

### Electrical Specification

#### DC Characteristics

Parameter	Conditions	Min	Typ	Max	Unit
Breakdown Voltage V <sub>(BR)DSS</sub>	V <sub>gs</sub> = -10V, I <sub>ds</sub> =48mA	130	-	-	V
Gate-Source Threshold Voltage V <sub>GS(th)</sub>	V <sub>ds</sub> =10V, I <sub>ds</sub> =48mA	-	-2.6	-	V
Drain Leakage Current I <sub>DSS</sub>	V <sub>gs</sub> = -10V, V <sub>ds</sub> =50V	-	-	19.2	mA
Gate Leakage Current I <sub>GSS</sub>	V <sub>gs</sub> =-10V, V <sub>ds</sub> =0V	-	-	4.8	mA

### Load Mismatch Test

Condition	Test Result
VSWR=10:1 at all Phase Angles, $V_{DD} = +48V_{dc}$ , $I_{DQ}=100mA$ , $P_{AVG} = 300W$ , PW = 100us, Duty Cycle=10% , freq@2450 MHz	No Device Degradation

### Thermal Information

Parameter	Condition	Value (Typ)	Unit
Thermal Resistance Junction to Case ( $R_{TH}$ )	$T_j = 97^{\circ}C$ , measured under DC condition	0.38	$^{\circ}C / W$

### Load Pull Performance

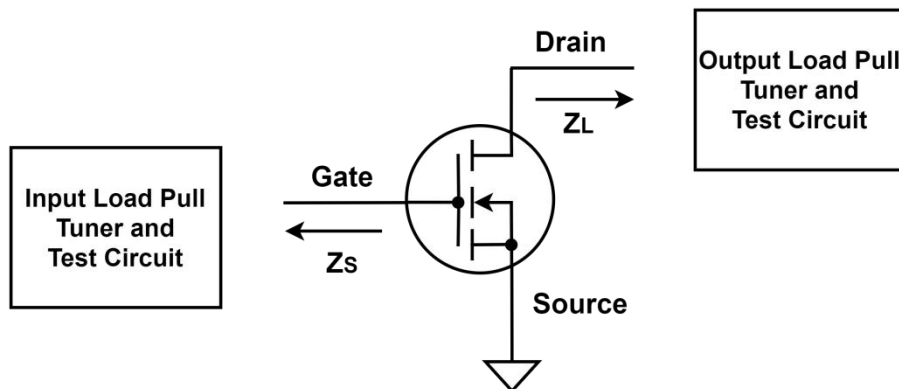
Test conditions unless otherwise noted:  $25^{\circ}C$ ,  $V_{DD} = +48V_{dc}$ ,  $I_{DQ} = 100mA$ , PW = 100us, Duty Cycle= 10%

Max Output Power						
Freq (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{load}$ [1] ( $\Omega$ )	Gain (dB)	P3dB (dBm)	P3dB (W)	Eff (%)
2400	$4.48+j*2.50$	$7.03-j*4.10$	18.90	57.02	503.50	64.74
2500	$2.10+j*1.86$	$7.70-j*3.59$	19.10	56.96	496.59	67.02

[1] Load impedance for optimum P3dB pout

Max Drain Efficiency						
Freq (MHz)	$Z_{source}$ ( $\Omega$ )	$Z_{load}$ [2] ( $\Omega$ )	Gain (dB)	P3dB (dBm)	P3dB (W)	Eff (%)
2400	$4.48+j*2.50$	$2.70-j*3.80$	20.31	55.20	331.13	75.58
2500	$2.10+j*1.86$	$2.96-j*5.10$	20.55	54.76	299.23	75.15

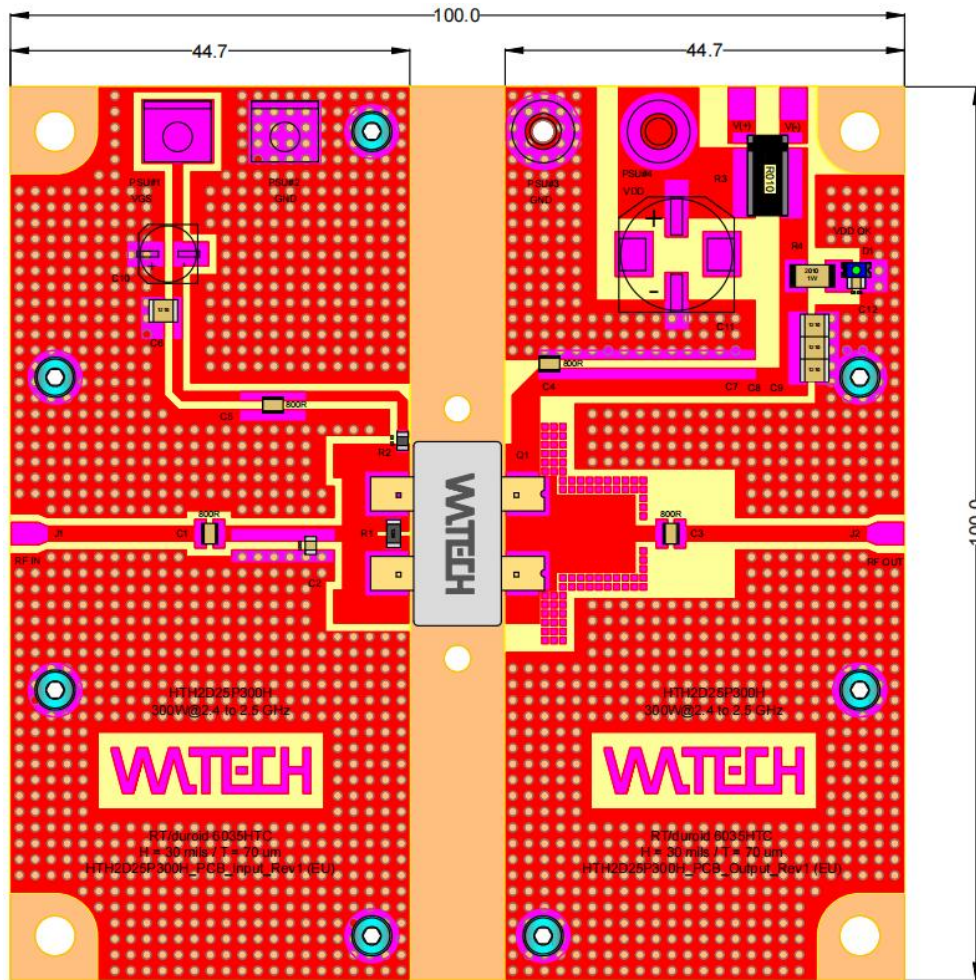
[2] Load impedance for optimum P3dB efficiency



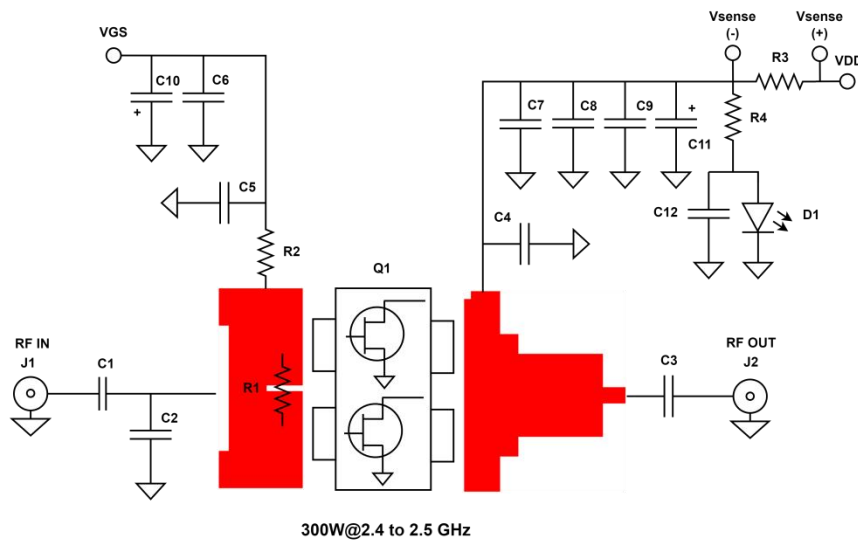
$Z_{source}$  : Measured impedance presented to the input of the device at the package reference plane

$Z_{load}$  : Measured impedance presented to the output of the device at the package reference plane

### HTH2D25P300H 2.4-2.5GHz Reference Design



**EVB Layout HTH2D25P300H @2.4-2.5GHz Reference Design**



**Schematic HTH2D25P300H @2.4-2.5GHz Reference Design**



# HTH2D25P300H

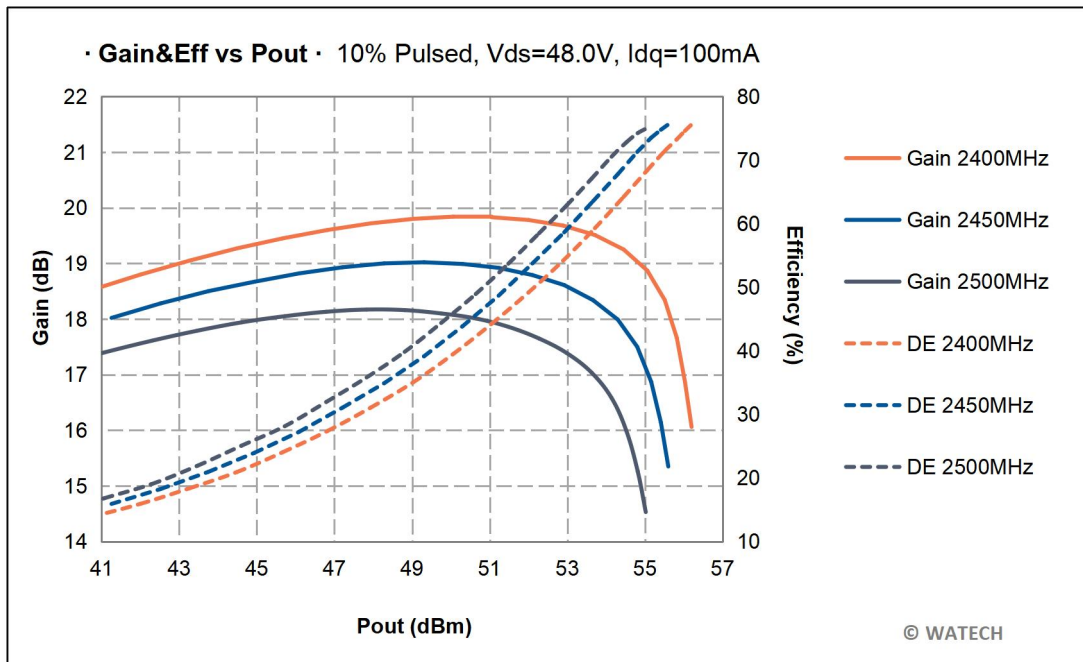
## 300W, 2.4 - 2.5 GHz GaN Amplifier

Product datasheet

### Bill of Materials (BoM) - HTH2D25P300H 2.4-2.5GHz Reference Design

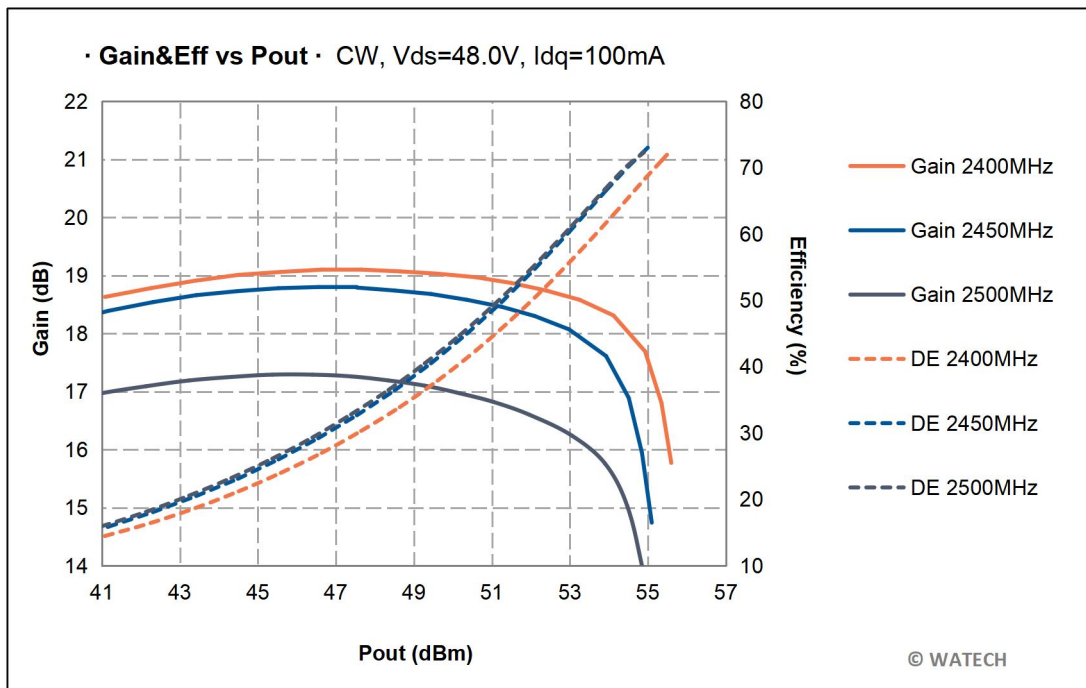
Reference	Value	Description	Manufacturer	P/N
Q1	-	300W, 2400 - 2500 MHz GaN on SiC Amplifier	WATECH	HTH2D25P300H
C1, C3, C4, C5	20pF/500VDC	MLCC	Beijing YuanLu	MQ101111M7G3A200JNMB
C2	2p2F/250VDC	GRM21A5C2E2R2FW01	Murata	GRM21A5C2E2R2FW01
C6, C8,C9	10uF/100VDC/1210	MLCC	Murata GRM	GRM32EC72A106KE05L
C7	390pF/500VDC/1210	MLCC	Beijing YuanLu	MQ101111M7G3A391JNMB
C11	22uF/35VDC	Aluminium Electrolytic Capacitor SMD	Nichicon	UWT1V220MCL1GB
C12	470uF/100VDC	Aluminium Electrolytic Capacitor SMD	Vishay	MAL215099913E3
R1	5.6Ω/1206	Thick Film Resistor	KOA	RK73B2BTDD5R6J
R2	12Ω/0805	Thick Film Resistor	KOA	RK73B2ATDD120J
<b>Diode Circuit</b>				
D1	1206 w/LENS GREEN 570nm	Standard LED - SMD	Dialight	599-0460-127F
R4	1K3Ω/1%/1206	Thick Film Resistor	Vishay	CRCW12061K30FKEAHP
C12	1nF/250VDC/0805	MLCC	TDK	C2012X7R2E102M085AE
<b>Connectors and PCB</b>				
PSU#1, PSU#2	n/a	Terminals .250 FAST TAB	TE Connectivity	42117-2
PSU#3, PSU#4	n/a	Terminals WPSMBU SMT Bush Type A M3 Thread	Wurth Elektronik	7466003
J1, J2	n/a	N-type Panel Connector (F)	Amphenol	172228
PCB	RT/Duroid 6035HTC (er = 3.5 ± 0.05), 30 mil (0.762 mm), 70 μm (2oz)			

### Performance Plots



**Pulsed CW, Gain & Eff vs Pout**

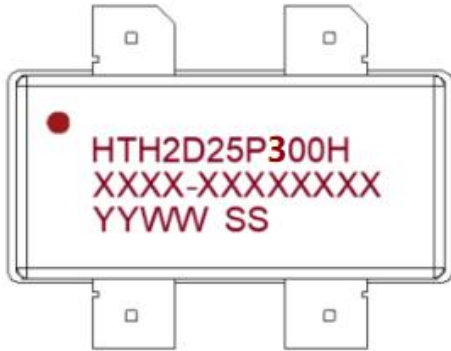
Test conditions unless otherwise noted: 25 °C, VDD = +48Vdc, IDQ = 100 mA, PW = 100us, Duty Cycle= 10%, tested on WATECH Application Board



**CW, Gain & Eff vs Pout**

Test conditions unless otherwise noted: 25 °C, VDD = +48Vdc, IDQ = 100 mA, CW, tested on WATECH Application Board

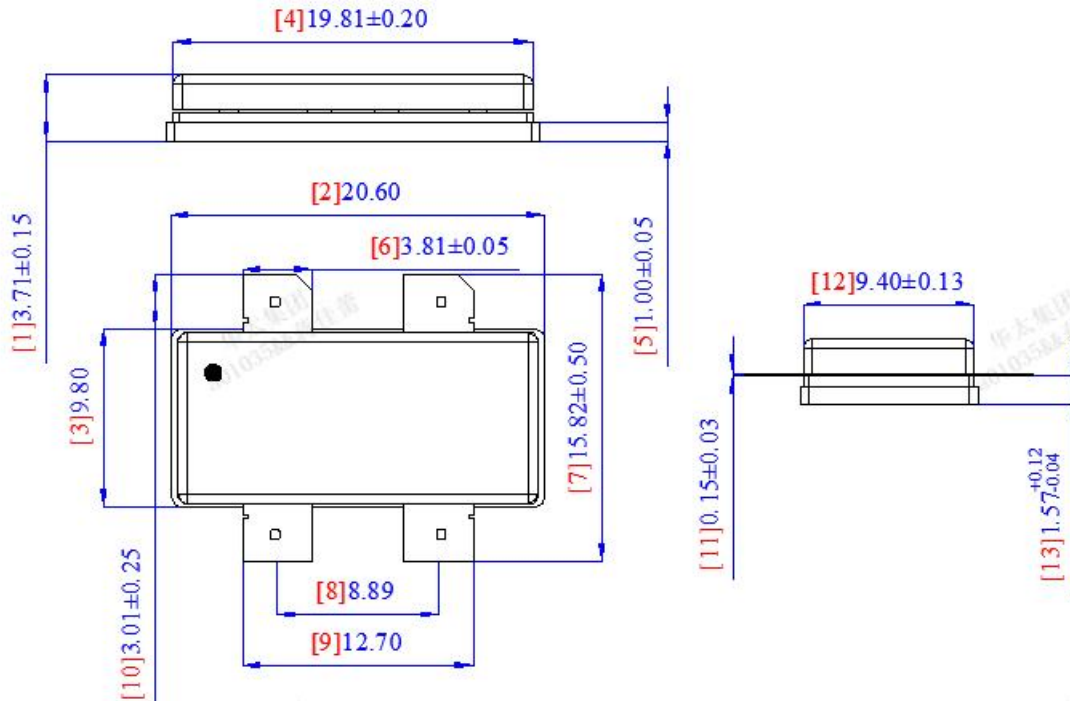
### Package Marking and Dimensions



- Line1 (fixed): Device name in work order
- Line2 (unfixed): Mark Lot number in work order (Sample: E596-EERA0001)
- Line3 (unfixed): Date Code + "SS" (The last two digits of sub lot Number)

This Marking SPEC only stipulates the content of Marking. For marking requirements such as font and size, please refer to the latest version of "Watech Product Printing Specification"

#### Marking



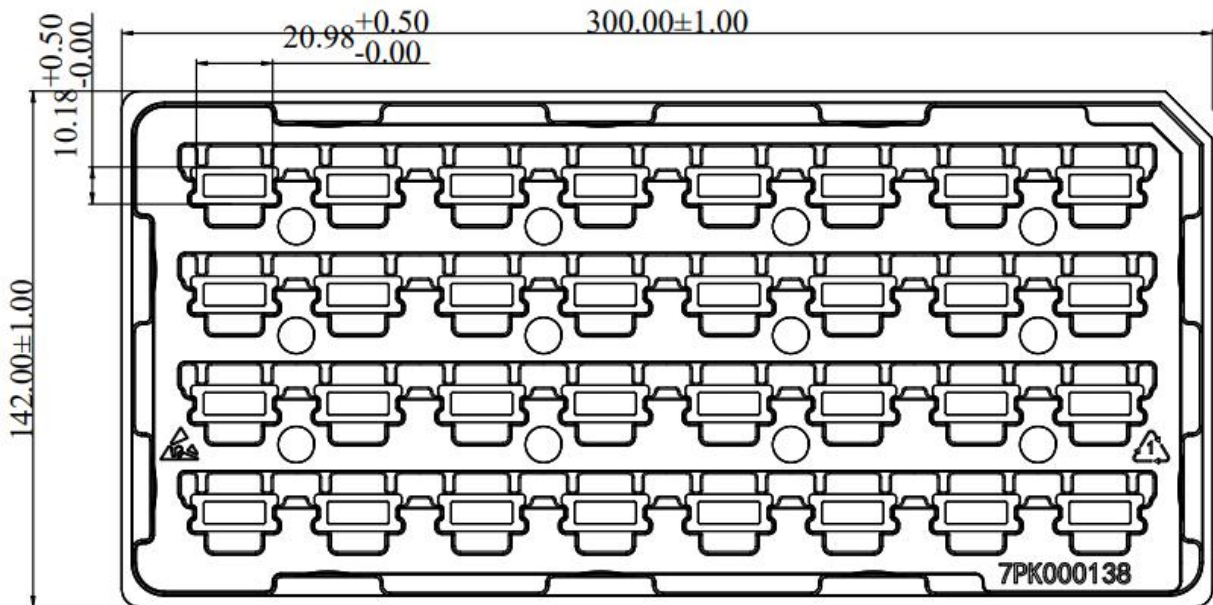
#### Package Dimensions

ACC2110S-4L Earless Flanged Balanced Air Cavity Ceramic Package; 4 leads

### Packing Information

#### HTH2D25P300H:

Package Type	Qty/Tray(pcs)	Qty/Box(pcs)	Qty/Carton(pcs)
ACC2110S-4L	32	160	960



#### Packaging Descriptions

### Handling Precautions

Parameter	Rating	Standard
ESD – Human Body Model (HBM)	Class 1B	JESD22-A114
ESD – Human Body Model (MM)	Class A	EIA/JESD22-A115
ESD – Charged Device Model (CDM)	Class III	JESD22-C101

### RoHS Compliance

This product is compliant with the 2011/65/EU RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment), as amended by Directive 2015/863/EU.





## Datasheet Status

---

Document status	Product status	Definition
Objective Datasheet	Design simulation	Product objective specification
Preliminary Datasheet	Customer sample	Engineering samples and first test results
Product Datasheet	Mass production	Final product specification

## Abbreviations

---

Acronym	Definition
GaN	Gallium Nitride
CW	Continuous Waveform

## Revision history

---

Document ID	Datasheet Status	Release Date	Revision Version
Rev 1.0	Product	Jun.2024	Product version datasheet
Rev 1.1	Product	Jun.2024	Update CW test plot
Rev 1.2	Product	Jun.2024	New product version datasheet



# HTH2D25P300H

## 300W, 2.4 - 2.5 GHz GaN Amplifier

Product datasheet

### Contact Information

---

For the latest specifications, additional product information, worldwide sales and distribution locations and information about WATECH:

- Web: [www.watechelectronics.com](http://www.watechelectronics.com)
- Email: [MKT@huatai-elec.com](mailto:MKT@huatai-elec.com)

For technical questions and application information:

- Email: [MKT@huatai-elec.com](mailto:MKT@huatai-elec.com)

### Important Notice

---

Information in this document is believed to be accurate and reliable. However, WATECH does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

“Typical” parameters are the average values expected by WATECH in large quantities and are provided for information purposes only. All information and specifications contained herein are subject to change without notice and customers should obtain and verify the latest relevant information before placing orders for WATECH products.

The information contained herein or any use of such information does not grant, explicitly or implicitly, to any party any patent rights, licenses, or any other intellectual property rights, whether with regard to such information itself or anything described by such information.

Applications that are described herein for any of these products are for illustrative purposes only. WATECH makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification. Customers are responsible for the design and operation of their applications and products using WATECH products, and WATECH accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the WATECH product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third-party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

WATECH products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of a WATECH product can reasonably be expected to result in personal injury, death or severe property or environmental damage. This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.